INTERNATIONAL SEARCH REPORT

International application No.
PCT/JP2004/015270

			
A. CLASSIFIC Int.Cl	CATION OF SUBJECT MATTER H01L33/00, H01L21/205		
According to In	ternational Patent Classification (IPC) or to both nation	al classification and IPC	
B. FIELDS SE	EARCHED		
Minimum docur	nentation searched (classification system followed by c H01L33/00, H01S5/00-5/50	classification symbols)	
Jitsuyo		ent that such documents are included in th Oroku Jitsuyo Shinan Koho itsuyo Shinan Toroku Koho	e fields searched 1994–2004 1996–2004
Electronic data	base consulted during the international search (name of	data base and, where practicable, search t	erms used)
C. DOCUME	NTS CONSIDERED TO BE RELEVANT		γ
Category*	Citation of document, with indication, where ap		Relevant to claim No.
Y	JP 2002-237617 A (Toshiba Co 23 August, 2002 (23.08.02), Par. Nos. [0020], [0025] to & JP 04-212479 A & US & JP 2000-058910 A	_	1-11
Y	JP 04-354382 A (Shin-Etsu Ha 08 December, 1992 (08.12.92), Full text (Family: none)		1-11
Y	HUANG et al., 'Twofold efficient in high performance AlGaInP diodes in 555-620 nmspectral thick GaP window layer', Appl Vol.61, pages 1045 to 1047	light-emitting region using a	1,2
× Further do	ocuments are listed in the continuation of Box C.	See patent family annex.	
* Special categories of cited documents: document defining the general state of the art which is not considered to be of particular relevance "E" earlier application or patent but published on or after the international filing date "L" document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified) "O" document referring to an oral disclosure, use, exhibition or other means document published prior to the international filing date but later than the priority date claimed		"T" later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone "Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art "&" document member of the same patent family	
Date of the actual completion of the international search 20 December, 2004 (20.12.04)		Date of mailing of the international search report 18 January, 2005 (18.01.05)	
	ng address of the ISA/ se Patent Office	Authorized officer	
Facsimile No.	0 (second sheet) (January 2004)	Telephone No.	

INTERNATIONAL SEARCH REPORT

International application No.
PCT/JP2004/015270

			2004/013270
A. CLASSIFIC	CATION OF SUBJECT MATTER HO1L33/00, H01L21/205		
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Ji tsuvo		ent that such documents are included in the oroku Jitsuyo Shinan Koho itsuyo Shinan Toroku Koho	e fields searched 1994–2004 1996–2004
Electronic data b	pase consulted during the international search (name of	data base and, where practicable, search to	erms used)
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filing date	cation or patent but published on or after the international	"X" document of particular relevance; the cl considered novel or cannot be conside step when the document is taken alone	
 "L" document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified) "O" document referring to an oral disclosure, use, exhibition or other means "P" document published prior to the international filing date but later than the priority date claimed 		"Y" document of particular relevance; the cl considered to involve an inventive s	
		combined with one or more other such documents, such combinate being obvious to a person skilled in the art "&" document member of the same patent family	
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	PCI/UP	2004/015270		
C (Continuation). DOCUMENTS CONSIDERED TO BE RELEVANT				
Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.		
Υ .	JP 10-065210 A (Mitsubishi Cable Industries, Ltd.), 06 March, 1998 (06.03.98), Par. Nos. [0034] to [0037], [0048]; Figs. 1, 2 (Family: none)	3,6		
Y	JP 06-296040 A (Sharp Corp.), 21 October, 1994 (21.10.94), Full text; Figs. 2, 5 & EP 0611131 A1 & US 5403916 A1	5,9		
Y	KISH et al., 'Very high-efficiency semiconductor wafer-bonded transparent-substrate (Al _x Ga _{1-x}) _{0.5} In _{0.5} P/GaP light-emitting diodes', Appl. Phys.Lett., 1994, Vol.64, pages 2839 to 2841	2,4,6,9		